DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 May 26 2003 Mar 20



FEATURES

- Small plastic SMD package
- Switching speed: max. 50 ns
- · General application
- Continuous reverse voltage: max. 100 V; 150 V; 200 V
- Repetitive peak reverse voltage: max. 120 V; 200 V; 250 V
- Repetitive peak forward current: max. 625 mA.

APPLICATIONS

• General purpose switching in e.g. surface mounted circuits.

DESCRIPTION

The BAS19, BAS20 and BAS21 are general purpose diodes fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE (1)
BAS19	JP*
BAS20	JR*
BAS21	JS*

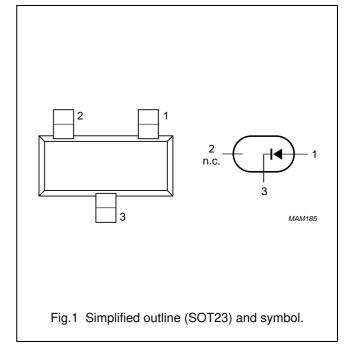
Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

PINNING

PIN	DESCRIPTION	
1	anode	
2	not connected	
3	cathode	

BAS19; BAS20; BAS21



BAS19; BAS20; BAS21

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage				
	BAS19		-	120	V
	BAS20		-	200	V
	BAS21		-	250	V
V _R	continuous reverse voltage				
	BAS19		-	100	V
	BAS20		-	150	V
	BAS21		-	200	V
l _F	continuous forward current	see Fig.2; note 1	-	200	mA
I _{FRM}	repetitive peak forward current		-	625	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	-	9	А
		t = 100 μs	-	3	А
		t = 10 ms	-	1.7	А
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

BAS19; BAS20; BAS21

ELECTRICAL CHARACTERISTICS

 $T_j = 25 \ ^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.3		
		I _F = 100 mA	1	V
		I _F = 200 mA	1.25	V
I _R	reverse current	see Fig.5		
	BAS19	V _R = 100 V	100	nA
		V _R = 100 V; T _j = 150 °C	100	μA
	BAS20	V _R = 150 V	100	nA
		V _R = 150 V; T _j = 150 °C	100	μA
	BAS21	V _R = 200 V	100	nA
		V _R = 200 V; T _j = 150 °C	100	μA
Cd	diode capacitance	$f = 1 \text{ MHz}; V_R = 0; \text{see Fig.6}$	5	pF
t _{rr}	reverse recovery time	when switched from I _F = 30 mA to I _R = 30 mA; R _L = 100 Ω ; measured at I _R = 3 mA; see Fig.8	50	ns

THERMAL CHARACTERISTICS

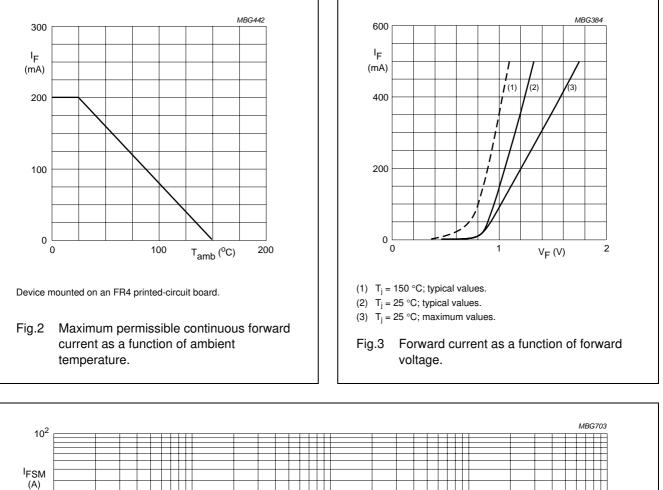
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		330	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

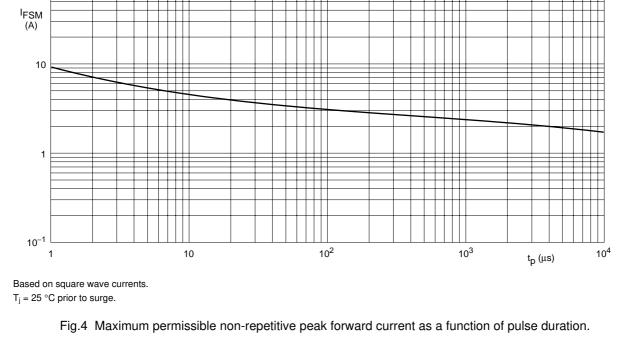
Note

1. Device mounted on an FR4 printed-circuit board.

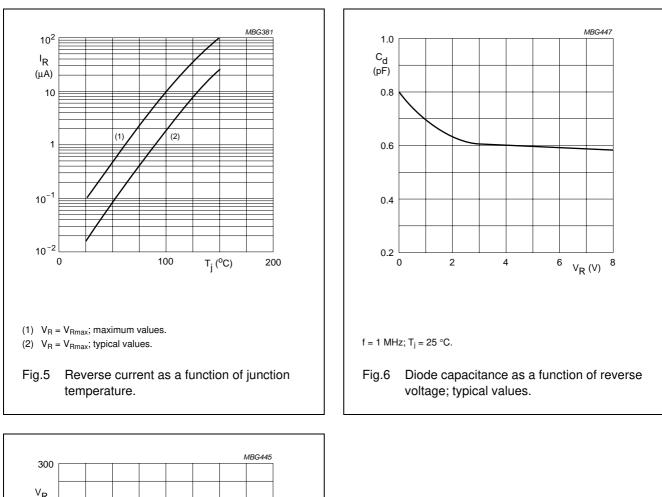
BAS19; BAS20; BAS21

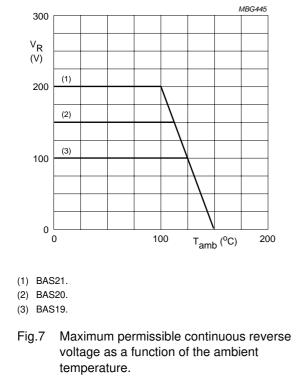
GRAPHICAL DATA



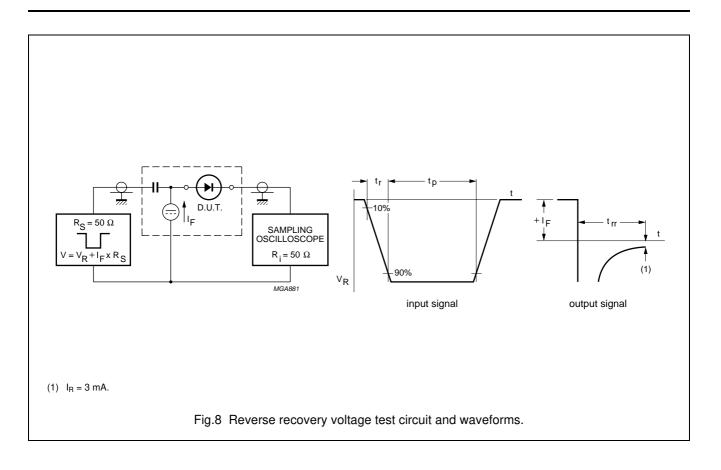


BAS19; BAS20; BAS21





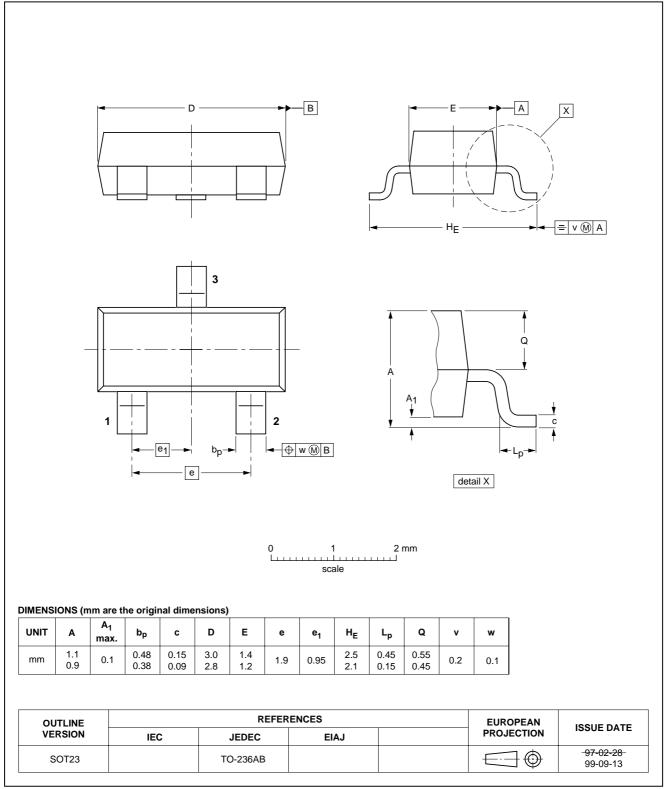
BAS19; BAS20; BAS21



BAS19; BAS20; BAS21

PACKAGE OUTLINE





BAS19; BAS20; BAS21

DATA SHEET	STATUS
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DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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